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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



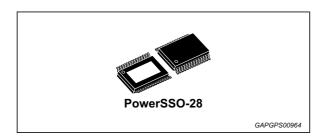






Automotive octal self configuring low/high side driver

Datasheet - production data



Features



- AEC-Q100 (Rev. F) qualified
- Eight independently self configuring low/high drivers
- Supply voltage from 4.5 V to 5.5 V
- $R_{ON(max)} = 0.7 \Omega @ T_j = 25 °C,$ $R_{ON(max)} = 1.2 \Omega @ T_i = 125 °C$
- · Minimum current limit of each output 1 A
- Output voltage clamping min. 40 V in low-side configuration
- Output voltage clamping max. -14 V in high-side configuration
- SPI interface for outputs control and for diagnosis data communication
- Additional PWM inputs for 3 outputs
- Independent thermal shutdown for all outputs open load, short to GND, short to Vb, overcurrent diagnostics in latched or unlatched mode for each channel
- Internal charge pump without need of external capacitor

Controlled SR for reduced EMC

Description

The L9733 is a highly flexible monolithic, medium current, output driver that incorporates 8 outputs that can be used as either internal low or high-side drives in any combination.

Outputs 1-8 are self-configuring as high or lowside drives. Self-configuration allows a user to connect a high or low-side load to any of these outputs and the L9733 will drive them correctly as well as provide proper fault mode operation with no other needed inputs. In addition, outputs 6, 7 and 8 can be PWM controlled via a external pins (IN6-8).

This device is capable of switching variable load currents over the ambient range of -40 °C to +125 °C. The outputs are MOSFET drivers to minimize Vdd current requirements. For low-side configured outputs an internal zener clamp from the drain to gate with a breakdown of 50 V minimum will provide fast turn off of inductive loads. When a high-side configured output is commanded Off after having been commanded On, the source voltage will go to (VGND - 15 V).

An 16 bit SPI input is used to command the 8 output drivers either "On" or "Off", reducing the I/O port requirement of the microcontroller. Multiple L9733 can be daisy-chained. In addition the SPI output indicates latched fault conditions that may have occurred.

Table 1. Device summary

Order code	Package Packing			
L9733XP	PowerSSO-28 (Exposed pad)	Tube		
L9733XPTR	PowerSSO-28 (Exposed pad)	Tape and reel		
L9733CN	PowerSSO-28 (Exposed pad)	Tube		
L9733CNTR	PowerSSO-28 (Exposed pad)	Tape and reel		

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Pin description L9733

1 Pin description

Figure 1. Pin connection (top view)

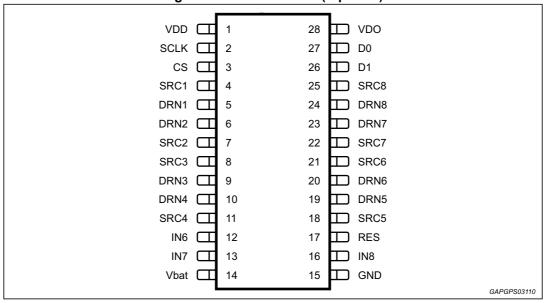


Table 2. Pin description

	Table 2.1 in description			
N°	Pin	Function		
1	VDD	5 Volt supply input		
2	SCLK	SPI serial clock input		
3	CS	SPI chip select (active low)		
4	SRC1	Source pin of configurable driver #1 (0.7 Ω Rds _{on} @ +25 °C)		
5	DRN1	Drain pin of configurable driver #1(0.7 Ω Rds _{on} @ +25 °C)		
6	DRN2	Drain pin of configurable driver #2 (0.7 Ω Rds _{on} @ +25 °C)		
7	SRC2	Source pin of configurable driver #2 (0.7 Ω Rds _{on} @ +25 °C)		
8	SRC3	Source pin of configurable driver #3 (0.7 Ω Rds _{on} @ +25 °C)		
9	DRN3	Drain pin of configurable driver #3 (0.7 Ω Rds _{on} @ +25 °C)		
10	DRN4	Drain pin of configurable driver #4 (0.7 Ω Rds _{on} @ +25 °C)		
11	SRC4	Source pin of configurable driver #4 (0.7 Ω Rds _{on} @ +25 °C)		
12	IN6	Discrete input used to PWM output driver #6		
13	IN7	Discrete input used to PWM output driver #7		
14	Vbat	Battery supply voltage		
15	GND	Analog ground		
16	IN8	Discrete input used to PWM output driver #8		
17	RES	Reset input (active low)		
18	SRC5	Source pin of configurable driver #5 (0.7 Ω Rds _{on} @ +25 °C)		

L9733 Pin description

Table 2. Pin description (continued)

N°	Pin	Function
19	DRN5	Drain pin of configurable driver #5 (0.7 Ω Rds _{on} @ +25 °C)
20	DRN6	Drain pin of configurable driver #6 (0.7 Ω Rds _{on} @ +25 °C)
21	SRC6	Source pin of configurable driver #6 (0.7 Ω Rds _{on} @ +25 °C)
22	SRC7	Source pin of configurable driver #7 (0.7 Ω Rds _{on} @ +25 °C)
23	DRN7	Drain pin of low-side driver #7 (0.7 Ω Rds _{on} @ +25 °C)
24	DRN8	Drain pin of low-side driver #8 (0.7 Ω Rds _{on} @ +25 °C)
25	SRC8	Source pin of configurable driver #8 (0.7 Ω Rds _{on} @ +25 °C)
26	DI	SPI data in
27	DO	SPI data out
28	VDO	Microcontroller logic interface voltage

Note: The exposed slug must be soldered on the PCB and connected to GND.

Operating conditions L9733

2 Operating conditions

2.1 Operating range

This part may not operate if taken outside the operating range. Once the condition is returned within the specified maximum rating or the power is recycled, the part will recover with no damage or degradation.

Symbol	Parameter	Value	Unit
V_{dd}	Supply voltage	4.5 to 5.5	V
V _{bat} (operative range)		4.5V to 18	
V _{bat} @ JSC		18 to 27	
V _{bat} @ low battery	Battery supply voltage	3.5 to 4.5	V
V _{bat} @ load dump		27 to 40	
T _j	Thermal junction temperature range	-40 to 150	°C
	Snubbing voltage of DRN1-8	min 50	VDC
I _{Ox}	Output current 1-8	max 800	mA
Eso	Maximum clamping energy at switch-off	20	mJ

Table 3. Operating range

2.1.1 Functional operative range

$$4.5 \text{ V} \le \text{V}_{\text{bat}} \le 18 \text{ V} \ (-40 \text{ °C} \le \text{T}_{\text{i}} \le 150 \text{ °C});$$

All the electrical capabilities are guaranteed by characterization as reported in *Section 3: Electrical performance characteristics*.

2.1.2 Jump start conditions

18
$$V \le V_{bat} \le 27 V (-40 \text{ °C} \le T_i \le 150 \text{ °C});$$

Operation at Jump start condition for a maximum duration of 1 minute.

All ouputs are switched according to the commands on the SPI bus or the PWM inputs. The SPI bus and the inputs are functional during the Jump-Start condition.

The over-temperature shutdown and over current protection of the device are not guaranteed to stay functional for Vbat between 18 V and 27 V.

The reliability and the functionality of the L9733XP are not compromised when the Jump-Start condition is not repeated for more than five times.

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2.1.3 Operation at low battery condition

$$3.5 \text{ V} \le \text{V}_{\text{bat}} \le 4.5 \text{ V} \text{ (-40 °C} \le \text{T}_{\text{j}} \le 150 °\text{C});$$

All outputs are able to keep the status according to the commands on the SPI bus or the PWM inputs. Switching commands entered via the SPI bus might not be executed by the L9733 at low-battery condition. The SPI bus and the inputs are functional during the Low-Battery condition.

2.1.4 Operation at load dump condition

$$27 \text{ V} \le \text{V}_{\text{bat}} \le 40 \text{ V} \ \ (-40 \text{ °C} \le \text{T}_{\text{j}} \le 150 \text{ °C})$$

There is not an internal circuit that switches OFF the drivers during load dump condition.

The over-temperature shutdown and over current protection of the device are not guaranteed to stay functional during load dump condition.

2.1.5 Loss of protection against short to battery

When the battery supply voltage, $V_{\text{bat (pin 14)}}$ is switched off during a short-to-battery condition at an output in high-side configuration, the protection circuits are no longer functional, and the L9733 may fail with EOS.

2.2 Absolute maximum ratings

This part may be irreparably damaged if taken outside the specified absolute maximum ratings. Operation outside the absolute maximum ratings may also cause a decrease in reliability.

Symbol Value Unit **Parameter** -0.3 to 7 ٧ V_{DD} Supply voltage Supply voltage -0.3 to 40 ٧ V_{bat} CS,DI,DO,SCLK,EN,IN6,IN7,IN8,VDO -0.3 to 7.0 ٧ SRCx pin min. -24 **VDC** Max. value of V_{SRCx} = Minimum of $\{V_{bat} + 1V \mid || V_{DRNx} + 0.3 V \mid || + 40 V\}$ DRN1-8⁽¹⁾ -0.3 to 60 **VDC** Current limit of output 1-8 (-40 °C) 25 Α I_{OL} Over current protection at output 1-8 (-40 °C) 3 Α I_{OP} 20 Maximum clamping energy mj ±2 (2) Human body model - All pins kV **ESD** ±4 (2) kV Human body model - Driver outputs

Table 4. Absolute maximum ratings



For the DRNx the MAX ASB value is the Max Clamp Voltage (see Table 6 on page 13 - DRNx Clamp voltage).

^{2.} Device is only protected vs. GND.

Operating conditions L9733

2.3 Thermal data

Table 5. Thermal data

Symbol	Parameter		Тур	Max	Unit
T _{amb}	Operating ambient temperature	-40	-	125	°C
T _{stg}	Storage temperature		-	150	°C
T _j	Maximum operating junction temperature		-	150	°C
R _{th}	Thermal shutdown temperature		175	200	°C
R _{th-hys}	Thermal shutdown temperature hysteresis		10	25	°C
R _{Th j-amb}	Thermal resistance junction-to-ambient (1)		-	24	°C/W
R _{Th j-case}	Thermal resistance junction-to-case	-	-	3	°C/W

^{1.} With 2s2p PCB thermally enhanced.



3 Electrical performance characteristics

These are the electrical capabilities this part was designed to meet. It is required that every part meets these characteristics.

3.1 DC characteristics

 T_{amb} = -40 to 125 °C, V_{dd} = 4.5 to 5.5 Vdc, V_{bat} = 4.5 to 18 Vdc (high-side configuration), unless otherwise specified.

Table 6. DC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Units
IN6v _{ih}	ING input voltage	-	-	-	0.7vdo	V
IN6v _{il}	IN6 input voltage	-	0.3vdo	-	-	V
I _{IN6iI}	ING input ourrent	In6 = 0 VDC	-	-	10	μΑ
I _{IN6ih}	IN6 input current	In6 = VDO	10	-	100	μΑ
IN7v _{ih}	INIZ input valtage	-	-	-	0.7vdo	V
IN7v _{il}	N7 input voltage	-	0.3vdo	-	-	V
I _{IN7iI}	INT input ourrent	In7 = 0 VDC	-	-	10	μΑ
I _{IN7ih}	IN7 input current	In7 = VDO	10	-	100	μΑ
IN8v _{ih}	IN8 input voltage	-	-	-	0.7vdo	V
IN8v _{il}		-	0.3vdo	-	-	V
I _{IN8iI}	- IN8 input current	In8 = 0 VDC	-	-	10	μΑ
I _{IN8ih}		In8 = VDO	10	-	100	μΑ
CS _{ih}	CC innut valtage	-	-	-	0.7vdo	V
CS _{il}	CS input voltage	-	0.3vdo	-	-	V
I _{CSih}	CC input surrent	CS = VDO	-	-	10	μΑ
I _{CSil}	CS input current	CS = 0 VDC	10	-	100	μΑ
SCLK _{ih}	0011/	-	-	-	0.7vdo	V
SCLK _{il}	SCLK input voltage	-	0.3vdo	-	-	V
I _{SCLKih}	CCL K innut surrent	SCLK = VDO	-	-	10	μΑ
I _{SCLKil}	SCLK input current	SCLK = 0 VDC	10	-	100	μΑ
DI _{ih}	Disputualtana	-	-	-	0.7vdo	V
DI _{il}	DI input voltage	-	0.3vdo	-	-	V
I _{Dlih}	Di innut surrent	DI = VDO	-	-	10	μΑ
I _{Dlil}	DI input current	DI = 0 VDC	10	-	100	μΑ
DO _{ol}	DO autout valtages	I _{DO} = 2.5 mA	-	-	0.4	V
DO _{oh}	DO output voltages	I _{DO} = -2.5 mA	vdo-0.6	-	-	V



Table 6. DC characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
I _{DOzol}	DO Tri state sumante	DO = 0 VDC	-	-	10	μA
I _{DOzoh}	DO Tri-state currents	DO = VDO	-	-	10	μA
RES _{ih}	DEC : t II	-	-	-	0.7vdo	V
RES _{il}	RES input voltage	-	0.3vdo	-	-	V
I _{RESil}	DEC is not somet	RES = 0 VDC	10	-	100	μА
I _{RESih}	RES input current	RES = VDO	-	-	10	μА
		@ -40 °C	2.8	-	4.2	
POR _{th}	Power on reset threshold	@ 25 °C	2.8	-	3.7	V
		@ 125 °C	2	-	3.4	
I _{slp}	Vbat sleep current	VDD = SRC1-8 = 0VDC DRN1-DRN8=18VDC, Vb. Sum currents (T _{amb} > 0 °C) (T _{amb} @ -40 °C)	-	-	10 3	μΑ μΑ
I _{vbat}	Vbat current	VDD = 5 V All Outputs Commanded On	-	-	15	mA
I _{VDD}	Max. VDD current	All Outputs Commanded On	-	-	8.5	mA
I _{VDD}	Min. VDD current	All Outputs Commanded Off	0.5	-		mA
I _{DRN1Ik} - I _{DRN8Ik}	DRN1 - DRN8 leakage currents (low-side)	VDD = 0 VDC: SRC1-8 = 0 VDC DRN1- DRN8 = 16 VDC DRN1- DRN8 = 40 VDC	-	-	5 10	μ Α μ Α
I _{SRC1lk} - I _{SRC8lk} .	SRC1 – SRC8 Leakage currents (high-side)	VDD = 0 VDC: SRC1-8 = 0 VDC DRN1- 8 = 16 V DRN1- 8 = 40 VDC	-	-	-5 -10	μ Α μ Α
I _{Drn1-8sink}	DRN1 – DRN8 sink current (low-side)	SRC1-8 = GND DI = AC00h $R_{load} \le 11 \text{ k}\Omega$ $R_{load} \le 200 \text{ k}\Omega$	10 120	-	100 280	μA μA
R _{DRN1-8}	Open load detection resistance	VBAT ≥ 9 V	11	-	200	ΚΩ
I _{Drn1-8source}	Source current	DRN1-DRN8 = GND	-10	-	-100	μΑ
I _{src1-8sink}	SRC1 – SRC8 sink/source current	DRN1- 8 = Vb, DI = AC00h SCR1- 8 = Vb	10	-	100	μΑ
I _{src1-8source}	(high-side)	SCR1- 8 = GND	-18	-	-100	μΑ
Volunt	DRN1 – DRN8 open load voltage	SRC1- 8 = GND, DI = AC00h DRN1- DRN8 = Open VDD=4.9 to 5.1 VDC	2.7	-	3.1	>
V _{Drn1-8open}	(low-side)	SRC1- 8 = GND, DI = AC00h DRN1- DRN8 = Open VDD = 4.5 to 5.5 V	2.5	-	3.5	V



Table 6. DC characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{src1-8open}	SRC1 – SRC8 open load voltage (High-side) DRN1 - DRN8	DRN1-8 = Vb, DI = AC00h SCR1-8 = open	2.0	-	2.8	V
I _{DRN1limit} - I _{DRN8limit}	DRN1 - DRN8 current limits (low-side)	DI = ACFFh, DI = AAFFh SRC1 - SRC8 = 0 VDC DRN1 - DRN8 = 4.5 - 16 VDC (T _{amb} > 0 °C) (T _{amb} @ -40 °C)	1 1	-	2.2 2.5	A A
I _{DRN10VC} - I _{DRN80VC}	DRN1 - DRN8 overcurrent threshold (low-side)	DI = AC00h, DI = AA00h SRC1 – SRC8 = 0 VDC DRN1 - DRN8 = 4.5 - 16 VDC (T _{amb} > 0 °C) (T _{amb} - 40 °C)	1	1	2.7 3	A A
I _{SRC1limit} - I _{SRC8limit}	SRC1 – SRC8 current limits (high-side)	DI = ACFFh, DI = AAFFh DRN1 - DRN8 = Vb SRC1 - SRC8 = GND (T _{amb} > 0 °C) (T _{amb} - 40 °C)	1	-	2.2 2.5	A A
I _{SRC10VC} - I _{SRC80VC}	Overcurrent threshold (high-side)	DRN1 - DRN8 = Vbat SRC1 - SRC8 = GND (T _{amb} > 0 °C) (T _{amb} - 40 °C)	1 1	-	2.7 3	A A
DRN1 _{CI+} - DRN8 _{CI} +	DRN1 - DRN8 Clamp voltages (low-side)	DI = AC00h SRC1-8 = GND, I _{DRN1-8} = 350 mA	50	-	60	V
SRC1 _{CI+} - SRC8 _{CI} +	SRC1 – SRC8 Clamp voltages (High-side)	DI = AC00h DRN1-8 = Vbat, I _{SRC1-8} = -350 mA	-24	-	-14	V
V _{Drn1-8open} - DRN1- 8 _{VthGND}	Short to GND threshold distance from open load voltage (low-side)	SRC1 – SRC8 = GND: Decrease Drn1 - Drn8 until Faults are "Set"	0.3	-	0.7	V
DRN1- 8 _{VthVbat} - V _{Drn1-8open}	DRN1 - DRN8 Short to Vbat threshold distance from open load voltage (low-side)	DI = AC00h SRC1 – SRC8 = GND: Increase Drn1 - Drn8 until Faults are "Not Set"	0.3	-	0.7	V
V _{Drn1-8open} - SRC1- 8 _{VthGND}	SRC1 - SRC8 Short to GND threshold distance from open load voltage (High-side)	DI = AC00h Drn1 – Drn8 = Vb: Decrease SRC1 - SRC8 until Faults are "Not Set"	0.2	-	0.6	V
SRC1- 8 _{VthVbat} - V _{Drn1-8open}	SRC1 – SRC8 Short to Vbat threshold distance from open load voltage (High-side)	DI = AC00h Drn1 – Drn8 = Vbat: Increase SCR1 - SCR8 until Faults are " Set"	0.2	-	0.6	V



Symbol	Parameter	Conditions	Min	Тур	Max	Units
		@ +125 °C @ I _{DRN} = 350 mA	-	-	1.2	Ω
Rdson _{Drn1-8} ⁽¹⁾	On resistance (Drn to SRC1-8)	@ +25 °C @ IDRN = 350 mA	-	-	0.7	Ω
		@ -40 °C @ I _{DRN} = 350 mA	-	-	0.5	Ω
Drn1-8 _{ther} ⁽²⁾	Thermal shutdown temperature	DI = ACFFh, I _{Drn1-8} = 1 mA, SRC1 – SRC8 = GND, Increase temperature until Drn1 - Drn8 > 2 VDC, Verify DO Bits 0-15 are "Set"	151	-	200	°C
Drn1-8 _{hyst} ⁽²⁾	Hysteresis	Drn1 - Drn8 < 2 VDC	5	-	15	°C

Table 6. DC characteristics (continued)

3.2 AC characteristics

 T_{amb} = -40 to 125 °C, V_{dd} = 4.5 to 5.5 Vdc, V_{bat} = 4.5 to 18 Vdc, unless otherwise specified

Table 7. AC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Units
T _{filtDRN1-8}	DRN1 - DRN8 Open load & short to GND filter time (low-side) (Latch mode)	DI = AC00h, DI = A3FFh SRC1 – SRC8 = GND	300	-	900	μs
T _{filtSRC1-8}	SRC1 - SRC8 Open load & short to Vbat filter time (high-side) (Latch mode)	DI = AC00h, DI = A3FFh DRN1 – DRN8 = Vb	300	-	900	μѕ
T _{delDRN1-8}	DRN1 - DRN8 Overcurrent switch off delay (low-side)	DI = ACFFh, DI = AA00h SRC1 – SRC8 = GND	10	-	75	μs
T _{delSRC1-8}	SRC1 - SRC8 Overcurrent switch off delay (high-side)	DI = ACFFh, DI = AA00h DRN1 – DRN8 = Vb	10	-	75	μs
T _{res}	Restart time after overcurrent switch off time (Int)	DI = ACFFh, DI = AA00h	120	-	450	ms
Drn1-8 _{htol}	Slew rate turn on	Outputs loaded as Figure 4 See Figure 2	0.65	-	1.95	V/µs
Drn1-8 _{ltoh}	Turn off (low-side)	See Figure 2	0.5	-	1.5	V/µs



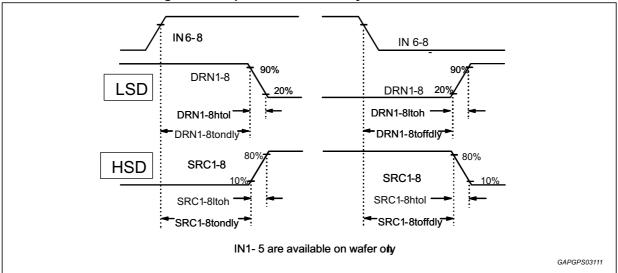
^{1.} $R_{dsonDrm1-8} \le$ 1.2 Ω ; at V_{bat} between 3.5 V and 27 V and T between -40 $^{\circ}C$ and 150 $^{\circ}C$

^{2.} Design Information, not tested.

Table 7. AC characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
SRC1-8 _{htol}	Slew rate turn on	Outputs loaded as Figure 4 See Figure 2	0.65	-	1.95	V/µs
SRC1-8 _{ltoh}	Turn off (High-side)	See Figure 2	0.5	-	1.5	V/µs
Drn1-8 _{tondly}	Delay time Turn on	Outputs loaded as Figure 4 See Figure 2	2	-	20	μs
Drn1-8 _{toffdly}	Turn off (low-side)	See Figure 2	10	-	100	μs
SRC1-8 _{tondly}	Delay time Turn on	Outputs loaded as Figure 4 See Figure 2	2	-	20	μs
SRC1-8 _{toffdly}	Turn off (high-side)	See Figure 2	10	-	100	μs
Drn1-8 _{offon}	Delay delta	Drn1-8 _{toffdly} - Drn1-8 _{tondly}	10	-	60	μs
SRC1-8 _{offon}	Delay delta	SRC1-8 _{toffdly} - SRC1-8 _{tondly}	10	-	60	μs

Figure 2. Output turn on/off delays and slew rates



3.3 SPI characteristics and timings

 T_{amb} = -40 to 125 °C, V_{dd} = 4.5 to 5.5 Vdc, V_{bat} = 4.5 to 18 Vdc, unless otherwise specified

Table 8. SPI characteristics and timings

Symbol	Parameter	Conditions	Min	Тур	Max	Units
DINC _{in}	Innut conscitones		-	-	20	pF
SCLK _{Cin}	Input capacitance	-	-	-	20	pF
DO _{rise}	Output data (do) rise time	50 pF from DO to Ground See <i>Figure 5</i>	-	-	70	ns
DO _{fall}	Output data (do) fall time	See Figure 5	-	-	70	ns
DOa	Access time	See Figure 6	-	-	350	ns
DO _{sum}	Set up time	See Figure 6	20	-	-	ns
DO _{hm}	Hold time	See Figure 6	10	-	-	ns
DO _{dis}	Output data (DO) disable time	No Capacitor on DO, See Figure 5	-	-	400	ns
tth _{Filt}	Filter time	All Fault bits are "Set"	5	-	20	μS
SCLKwid	SCLK width	See Figure 5, @ f _{SCLK} = 5.4MHz ⁽¹⁾	185	-	-	ns
SCLKIm	SCLK low time	See Figure 5, @ f _{SCLK} = 5.4MHz ⁽¹⁾	58	-	-	ns
SCLKhm	SCLK high time	See Figure 5, @ f _{SCLK} = 5.4MHz ⁽¹⁾	58	-	-	ns
SCLKrise	SCLK rise time	See Figure 5, @ f _{SCLK} = 5.4MHz ⁽¹⁾	-	-	21	ns
SCLKfall	SCLK fall time	See Figure 5, @ f _{SCLK} = 5.4MHz ⁽¹⁾	-	-	21	ns
CSrise	Channel select (CS) rise time	See Figure 5 ⁽¹⁾	-	-	100	ns
CSfall	Channel select (CS) fall time	See Figure 5 ⁽¹⁾	-	-	100	ns
CSlead	Channel select (CS) lead time	See Figure 6 (1)	455	-	-	ns
CSlag	Channel select (CS) lag time	See Figure 6 (1)	50	-	-	ns
DIrise	Input data (DI) rise time	See Figure 5, @ f _{SCLK} = 5.4MHz ⁽¹⁾	-	-	30	ns
DIfall	Input data (DI) fall time	See Figure 5 @ f _{SCLK} = 5.4MHz ⁽¹⁾	-	-	30	ns
Disus	Input data (DI) set-up time	See Figure 6, @ f _{SCLK} = 5.4MHz ⁽¹⁾	15	-	-	ns
DIhs	Input data (DI) hold time	See Figure 6, @ f _{SCLK} = 5.4MHz ⁽¹⁾	10	-	-	ns
CS2SCLK	CS rise to SCLK rise	See Figure 6, @ f _{SCLK} = 5.4MHz ⁽¹⁾	40	-	300	ns

^{1.} Guaranteed by design.

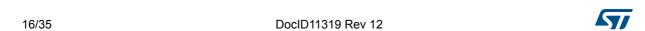


Figure 3. DO loading for disable time measurement

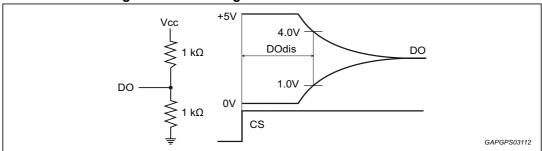


Figure 4. Output loading for slew rate measurements

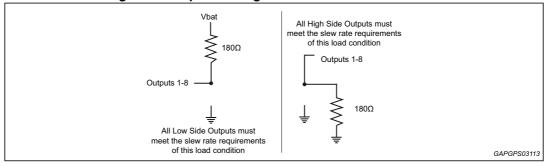


Figure 5. SPI input/output timings

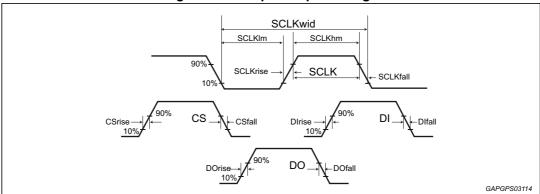
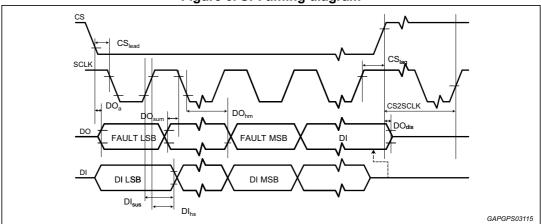


Figure 6. SPI timing diagram





Functional description 4

L9733 integrates 8 self-configuring outputs (OUT1-8) which are able to drive either incandescent lamps, inductive loads (non-pwm'd, in pwm an external diode to reduce flyback power dissipation is necessary), or resistive loads biased to Vbat (low-side configuration) or to GND (high-side configuration). These outputs can be enabled and disabled via the SPI bus. Each of these outputs has a short circuit protection (with 0.8-2.4 Amps threshold) selectable via SPI bus between a filtered switching OFF overcurrent protection or a linear current limitation (default condition after power ON is switching OFF protection enabled).

An over-temperature protection as described in Section 2.1 is available for each output. When a high-side configured output is commanded OFF after having been commanded ON. the source voltage will go to (VGND - 15 V). This is due to the design of the circuitry and the transconductance of the MOSFET. When a low-side configured output is commanded OFF after having been commanded ON, the output voltage will rise to the internal zener clamp voltage (50 VDC minimum) due to the flyback of the inductive load.

Outputs 1-8 are able to drive any combination of inductive loads or lamps at one time. Inductive loads for the L9733 can range from 35 mH to a maximum of 325 mH. The recommended worst-case solenoid loads (at -40 °C) are calculated using a minimum resistance of 40 Ω for each output. The maximum single pulse inductive load energy the L9733 output is able to be safely handled is 20 mJ at -40 °C to 125 °C (Worst-case load of 325 mH and 40 Ω).

4.1 **Configurations for outputs 1-8**

The drain and source pins for each output must be connected in one of the two following configurations (see Figure 7).

4.1.1 Low-side drivers

When any combination of outputs 1-8 are connected in a low-side drive configuration the source of the applicable output (Src1-8) shall be connected to ground. The drain of the applicable output (Drn1-8) shall be connected to the low-side of the load.

4.1.2 **High-side drivers**

When any combination of outputs 1-8 are connected in a high-side drive configuration the drain of the applicable output (Drn1-8) shall be connected to Vbat. The source of the applicable output (Src1-8) shall be connected to the high-side of the load.

4.2 **Outputs 1-5**

These five outputs can be used as either high or low-side drives. The room temperature Rdson of these outputs is 0.7 Ω A current limited (100 μA max) voltage generator is connected to Src 1-5 for open load and short to GND detection when a low-side configured output is commanded OFF. Another current limited (100 µA max if VDrn 1-5 > 60 %Vbat, 280 µA max if VDrn 1-5 < 60 % Vbat) voltage generator is connected to Drn 1-5 for open load and short to V bat detection when a high-side configured output is commanded OFF.

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Drain pins of outputs 1-5 (Drn1-5) are connected to the drains of the N channel MOSFET transistors. Source pins of outputs 1-5 (Src1-5) are connected to the sources of the N-channel MOSFET transistors.

4.3 Outputs 6-8

These three self-configuring outputs can be used to drive either high or low-side loads. In addition to being controlled by the SPI BUS these outputs can also be enabled and disabled via the IN6 & IN7& IN8 inputs. The IN6, IN7 and IN8 inputs are logically OR'd with the SPI commands to allow either the IN6 & IN7 & IN8 inputs or the SPI commands to activate these outputs. The use of the IN6 & IN7 & IN8 pins for PWM control on these outputs should only be done with non-inductive loads if an external flyback diode is not present. The room temperature Rdson of these four outputs is 0.7 Ω . A current limited (100 μ A max) voltage generator is connected to Src 6-8 for open load and short to GND detection when a low-side configured output is commanded OFF. Another current limited (100 μ A max if VDrn 6-8 > 60%Vbat, 280 μ A max if VDrn 6-8 < 60 %Vbat) voltage generator is connected to Drn 6-8 for open load and short to Vbat detection when a high-side configured output is commanded OFF.

Drain pins of Outputs 6-8 (Drn6-8) are connected to the drains of the N channel MOSFET transistors. Source pins of Outputs 6-8 (Src6-8) are connected to the sources of the N channel MOSFET transistors.

4.4 Drn1-8 susceptibility to negative voltage transients

All outputs connected in the low-side configuration must have a ceramic chip capacitor of 0.01 μ F to 0.1 μ F connected from drain to ground. This is needed to prevent potential problems with the device operation due to the presence of fast negative transient(s) on the drain(s) of the device. Adequate de-coupling capacitors from the Drain (VBAT) to ground shall be provided for high-side configured outputs.

4.5 Supply pins

4.5.1 Main power input (Vdd)

An external $+5.0 \pm 0.5$ VDC supply provided from an external source is the primary power source to the L9733. This supply is used as the power source for all of its internal logic circuitry and other miscellaneous functions.

4.5.2 Battery supply (Vbat)

This input is the supply for the on board charge pump. This input shall be connected directly to battery. If this input is not connected to the same supply, without additional voltage drops, of the drains of any high-side connected outputs, then the Rdson of that given output will be higher than the specified maximum.

4.5.3 Discrete inputs voltage supply (VDO)

This pin is used to supply the discrete input stages of L9733 and must be connected to the same voltage used to supply the peripherals of the processor interfaced to L9733.



4.6 Discrete inputs

4.6.1 Output 6-8 enable input (In6, In7, In8)

This input allows Output 6 (or Output 7, or Output 8) to be enabled via this external pin without the use of the SPI. The SPI command and the In6-7 input are logically OR'd together. A logic "1" on this input (In6, In7 or In8) is enable the corresponding output no matter what the status of the SPI command register is. A logic "0" on this input will disable this output if the SPI command register is not commanding this output on. This pins (In6, In7 or In8) can be left "open" if the internal output device is being controlled only via the SPI. This input has a nominal 100 k Ω resistor connected from this pin to ground, which will pull this pin to ground if an open circuit condition occurs. This input is ideally suited for non-inductive loads that are pulse width modulated (PWM'd). This allows PWM control without the use of the SPI inputs.

4.6.2 Reset input (RES)

When this input goes low it resets all the internal registers and switches off all the output stages. This input has a nominal 100 k Ω resistor connected from this pin to VDD, which will pull this pin to VDD if an open circuit condition occurs.



5 Serial peripheral interface (SPI)

The L9733 has a serial peripheral interface consisting of Serial Clock (SCLK), Data Out (DO), Data In (DI), and Chip Select (CS). All outputs will be controlled via the SPI. The input pins CS, SCLK, and DI, thanks to VDO pin, have level input voltages allowing proper operation from microcontrollers that are using 5.0 or 3.3 volts for their Vdd supply. The design of the L9733 allows a "daisy-chaining" of multiple L9733's to further reduce the need for controller pins.

5.1 Serial data output (DO)

This output pin is in a tri-state condition when CS is a logic '1'. When CS is a logic '0', this pin transmits 16 bits of data from the fault register to the digital controller. After the first 16 bits of DO fault data are transmitted (after a CS transition from a logic '1' to a logic '0'), then the DO output sequentially transmits the digital data that was just received (16 SCLK cycles earlier) on the DI pin. The DO output continues to transmit the 16 SCLK delayed bit data from the DI input until CS eventually transitions from a logic '0' to a logic '1'. DO data changes state 10 nsec or later, after the falling edge of SCLK. The LSB is the first bit of the byte transmitted on DO and the MSB is the last bit of the byte transmitted on DO, once CS transitions from a logic '1' to a logic '0'.

5.2 Serial data input (DI)

This input takes data from the digital controller while CS is low. The L9733 accepts a 16 bit byte to command the outputs on or off. The L9733 also serially wraps around the DI input bits to the DO output after the DO output transmits its 16 fault flag bits. The LSB is the first bit of each byte received on DI and the MSB is the last bit of each byte received on DI, once CS transitions from a logic '1' to a logic '0'. The last 4 bits (b15-b12) of the first 16 bit byte are used as key-word. The 4 bits (b11-b8) of the first 16 bits byte are used to select writing mode between OUT8-1 status and diagnosis operating mode . The DI input has a nominal 100 k Ω resistor connected from this pin to the VDO pin, which pulls this pin to VDO if an open circuit condition occurs.

5.3 Chip select (CS)

This is the chip select input pin. On the falling edge of CS, the DO pin is released from tristate mode. While CS is low, register data are shifted in and shifted out the DI pin and DO pin, respectively, on each subsequent SCLK. On the rising edge of CS, the DO pin is tristated and the fault register is "Cleared" if a valid DI byte has been received. A valid DI byte is defined as such:

- a multiple of 16 bits was received;
- a valid key-word was received.

The fault data is not cleared unless all of the 2 previous conditions have been met. The CS input has a nominal 100 k Ω resistor connected from this pin to the VDO pin, which pulls this pin to VDO if an open circuit condition occurs.



5.4 Serial clock (SCLK)

This is the clock signal input for synchronization of serial data transfer. DI data is shifted into the DI input on the rising edge of SCLK and DO data changes on the falling edge of SCLK. The SCLK input has a nominal 100 k Ω resistor connected from this pin to the VDO pin, which pulls this pin to VDO if an open circuit condition occurs.

5.5 Initial input command register and fault register SPI cycle

After initial application of Vdd to the L9733, the input command register and the fault register are "Cleared" by the POR circuitry and that means that the default condition for the output status is Off, the default diagnostic mode is No Latch and the switching OFF overcurrent protection is enable. During the initial SPI cycle, and all subsequent cycles, valid fault data will be clocked out of DO (fault bits).

5.6 Input command register

An input byte (16 bits) is routed to the Command Register. The content of this Command Register is given in *Table 10*. Additional DI data will continue to be wrapped around the DO pin. If CS should happen to go high before complete reception of the current byte, this just transmitted byte shall be ignored (invalid).

Table 9. Bit command register definition

											LIOII				
	Key	word		Writi	Writing mode: output Output status										
MSB					LSE							LSB			
1	0	1	0	1	1	0	0	OUT 8	OUT 7	OUT 6	OUT 5	OUT 4	OUT 3	OUT 2	OUT 1
b15	b14	b13	b12	b11	b10	b9	b8	b7	b6	b5	b4	b3	b2	b1	b0
	Key	word		Wri	ting m	ode: d	liag				river d	iag mo	de		
MSB								•							LSB
1	0	4		_	^	4	-1	D: 0	D:	D: 0	D:	D: 4	D: 0	- ·	. .
'	0	1	0	0	0	1	1	Diag 8	Diag 7	Diag 6	Diag 5	Diag 4	Diag 3	Diag 2	Diag 1
b15	b14	b13	b12	b11	b10	b9	b8	biag 8	b6	b5	b4	b3	biag 3	b1	biag 1
							-	-		_					_
	b14			b11		b9	b8	-	b6	b5	b4	b3		b1	_
	b14	b13		b11	b10	b9	b8	-	b6	b5	b4	b3	b2	b1	_
b15	b14	b13		b11	b10	b9	b8	-	b6	b5	b4	b3	b2	b1	b0



Table 10. Command register logic definition

Bit	State	Status	Writing mode
b0-b7	0	OUT1 - OUT8 are commanded off	Output
b0-b7	1	OUT1 - OUT8 are commanded on	Output
b0-b7	0	OUT1 - OUT8 diagnostic is No Latch Mode	Diag
b0-b7	1	OUT1 - OUT8 diagnostic is Latch Mode	Diag
b0-b7	0	OUT1 - OUT8 switching OFF overcurrent protection	Protection
b0-b7	1	OUT1 - OUT8 linear overcurrent protection	Protection



Other L9733 features L9733

6 Other L9733 features

6.1 Charge pump usage

In order to provide low Rdson values when connected in a high-side configuration, a charge pump to drive the internal gate voltage(s) above Vbat is implemented. The charge pump used on the L9733 doesn't need external capacitor. The L9733 uses a common charge pump and oscillator for all the 8 configurable output channels. The charge pump uses the Vbat supply connected directly to the Vb pin. The normal range of the Vbat voltage is 10 to 18V18V. However, the L9733 is functional with Vbat voltages as low as 4.5 V DC with eventually a degradation of Rdson.

The frequency range of this charge pump is from 3.6 to 7.6 MHz. The frequency is above 1.8 MHz in order to be above the AM radio band and below 8.0 MHz so that harmonics do not get within the FM radio band.

6.2 Waveshaping

Both the turn on and the turn off slew rates on all outputs (OUT1-8) are limited to between $10 \mu s$ and $100 \mu s$ for both rise and fall times (10 to 90 %, and vice versa), to reduce conducted EMC energy in the vehicle's wiring harness. The characteristics of the turn-on and turn-off voltage is linear, with no discontinuities, during the output driver state transition.

6.3 POR register initialization

When the L9733 wakes up, the Vdd supply to the L9733 is allowed from 0 to 5 VDC in 0.3 to 3ms. The L9733 has a POR circuit, which monitors the Vdd voltage. When the Vdd voltage reaches an internal threshold, and remains above this trip level for at least 5 to 20 μ s, the Command and Fault registers are "cleared". Before Vdd reaches this trip level, none of the eight outputs are allowed to momentarily glitch on.

6.4 Thermal shutdown

Each of the eight outputs has independent thermal protection circuitry that disables each output driver once the local N-Channel MOSFET's device temperature reaches between +151 and +200 °C. A filter is present to validate the thermal fault (5 μ s to 20 μ s). There is a 5 to 15 °C hysteresis between the enable and disable temperature levels. The faulted channel will periodically turn off and on until the fault condition is cleared, the ambient temperature is decreased sufficiently or the output is commanded off. If a thermal shutdown, of one or more output drivers, is active during the falling edge of the chip select (CS) signal all the bits of the Fault Register are "set" to "1" (thermal shutdown is not latched and could be read only in the moment it is present). The thermal fault is cleared on the rising edge of Chip Select if a valid DI byte is received.

Note:

Due to the design of the L9733 each output's thermal limit "may not" be truly independent to the extent that if one output is shorted, it may impact the operation of other outputs (due to lateral heating in the die).

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L9733 Fault operation

7 Fault operation

The fault diagnostic capability consists of one internal 16 bits shift register and 2 bits are used for each output. The diagnostic information is: no fault present, overcurrent, open load and short circuit.

For L9733XP all of the faults will be cleared on the rising edge of chip select if a valid DI byte is received.

For L9733CN the OVC register are cleared when the end of the diagnosis restart time T_{res} is reached or by the input signal (IN) in low state. The other faults are cleared on the rising edge of chip select if a valid DI byte is received.

					IGNIC		aait i o	9.000	40						
OU	OUT 8		OUT 7		JT6	ΟL	IT5	OU	IT4	ου	IT3	ΟL	IT2	Ol	JT1
MSB															LSB
D1	D0	D1	D0	D1	D0	D1	D0	D1	D0	D1	D0	D1	D0	D1	D0
b15	b14	b13	b12	b11	b10	b9	b8	b7	b6	b5	b4	b3	b2	b1	b0

Table 11. Fault register definition

Table	12	Fault	logic	defin	ition
Iabic	14.	ı auıı	10410	aciii	

D1	D0	Fault status
0	0	No fault is present
0	1	Open load
1	0	Short circuit to GND (low-side) or short circuit to Vbat (high-side)
1	1	Overcurrent

If all the bits b0-b15 of the fault register have value '1' it means that a thermal fault, at least on one of the eight independent Outputs, occurred.

7.1 Low-side configured output fault operation

The diagnostic circuitry verifies for the low-side configured output the following condition: Normal operation, open load, short circuit to GND and overcurrent (only if the switching OFF protection, selectable for each channel via SPI bus, is active).

The diagnostic circuitry operates in two different modes, selected for each channel by SPI: no latch mode and latch mode. The fault priority is overcurrent and then open load or short circuit to GND, this means that if an overcurrent occurs the fault register is always overwritten and following open load or short to GND faults that happen before that the register is cleared will be ignored.